

MM54C200/MM74C200 256-Bit TRI-STATE® Random Access Read/Write Memory

General Description

The MM54C200/MM74C200 is a 256-bit random access read/write memory. Inputs consist of eight address lines, and three chip enables. The eight binary address inputs are decoded internally to select each of the 256 locations. The internal address register, latches, and address information are on the positive to negative edge of \overline{CE}_3 . The TRI-STATE® data output line, working in conjunction with \overline{CE}_1 or \overline{CE}_2 inputs, provides for easy memory expansion.

Address Operation: Address inputs must be stable t_{SA} prior to the positive to negative transition of \overline{CE}_3 . It is therefore unnecessary to hold address information stable for more than t_{HA} after the memory is enabled (positive to negative transition).

Note: The timing is different from the DM74200 in that a positive to negative transition of the \overline{CE}_3 must occur for the memory to be selected.

Read Operation: The data is read out by selecting the proper address and bringing $\overline{\text{CE}}_3$ low and $\overline{\text{WE}}$ high.

Holding either \overline{CE}_1 , \overline{CE}_2 , or \overline{CE}_3 at a high level forces the output into TRI-STATE. When used in bus-organized systems, \overline{CE}_1 , or \overline{CE}_2 , a TRI-STATE control provides for fast access times by not totally disabling the chip.

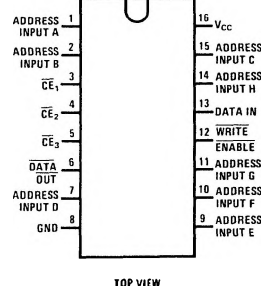
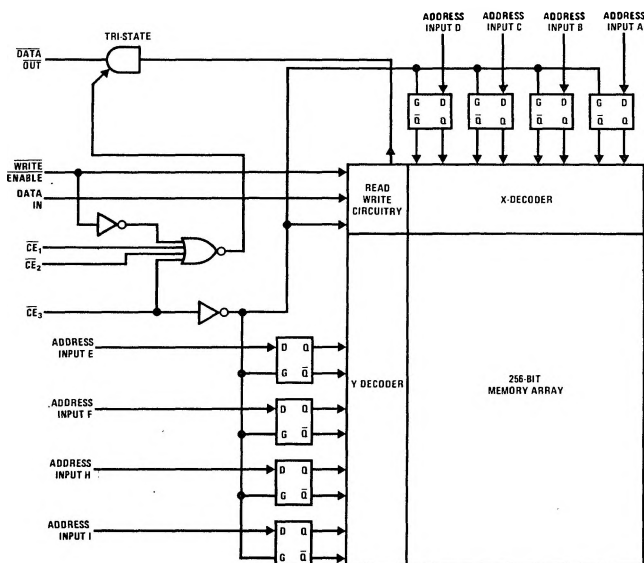
Write Operation: Data is written into the memory with \overline{CE}_3 low and \overline{WE} low. The state of \overline{CE}_1 or \overline{CE}_2 has no effect on the write cycle. The output assumes TRI-STATE with \overline{WE} low.

Features

- Wide supply voltage range 3.0V to 15V
- Guaranteed noise margin 1.0V
- High noise immunity 0.45 V_{CC} (typ.)
- TTL compatibility fan out of 1 driving standard TTL
- Low power 500 nW (typ.)
- Internal address register

TRI-STATE is a registered trademark of National Semiconductor Corp.

Logic and Connection Diagrams



**Order Number MM54C200D
or MM74C200D
See Package 3**

Order Number MM74C200N
See Package 15

Absolute Maximum Ratings (Note 1)

Voltage at Any Pin	-0.3V to $V_{CC} + 0.3V$
Operating Temperature Range	
MM54C200	-55°C to +125°C
MM74C200	-40°C to +85°C
Storage Temperature Range	-65°C to +150°C
Package Dissipation	500 mW
Operating V_{CC} Range	3.0V to 15V
Absolute Maximum V_{CC}	18V
Lead Temperature (Soldering, 10 seconds)	300°C

DC Electrical Characteristics Min./max. limits apply across temperature range, unless otherwise noted.

Parameter	Conditions	Min.	Typ.	Max.	Units
CMOS to CMOS					
$V_{IN(1)}$ Logical "1" Input Voltage	$V_{CC} = 5.0V$ $V_{CC} = 10V$	3.5 8.0			V V
$V_{IN(0)}$ Logical "0" Input Voltage	$V_{CC} = 5.0V$ $V_{CC} = 10V$			1.5 2.0	V V
$V_{OUT(1)}$ Logical "1" Output Voltage	$V_{CC} = 5.0V, I_O = -10\mu A$ $V_{CC} = 10V, I_O = -10\mu A$	4.5 9.0			V V
$V_{OUT(0)}$ Logical "0" Output Voltage	$V_{CC} = 5.0V, I_O = +10\mu A$ $V_{CC} = 10V, I_O = +10\mu A$			0.5 1.0	V V
$I_{IN(1)}$ Logical "1" Input Current	$V_{CC} = 15V, V_{IN} = 15V$		0.005	1.0	μA
$I_{IN(0)}$ Logical "0" Input Current	$V_{CC} = 15V, V_{IN} = 0V$	-1.0	-0.005		μA
I_{CC} Supply Current	$V_{CC} = 15V$		0.10	600	μA
CMOS/TTL Interface					
$V_{IN(1)}$ Logical "1" Input Voltage	54C $V_{CC} = 4.5V$ 74C $V_{CC} = 4.75V$	$V_{CC} - 1.5$ $V_{CC} - 1.5$			V V
$V_{IN(0)}$ Logical "0" Input Voltage	54C $V_{CC} = 4.5V$ 74C $V_{CC} = 4.75V$			0.8 0.8	V V
$V_{OUT(1)}$ Logical "1" Output Voltage	54C $V_{CC} = 4.5V, I_O = -1.6mA$ 74C $V_{CC} = 4.75, I_O = -1.6mA$	2.4 2.4			V V
$V_{OUT(0)}$ Logical "0" Output Voltage	54C $V_{CC} = 4.5V, I_O = 1.6mA$ 74C $V_{CC} = 4.75, I_O = 1.6mA$			0.4	V
Output Drive (See 54C/74C Family Characteristics Data Sheet) (Short Circuit Current)					
I_{SOURCE} Output Source Current (P-Channel)	$V_{CC} = 5.0V, V_{OUT} = 0V$ $T_A = 25^\circ C$	-4.0 -1.8	-6.0		mA mA
I_{SOURCE} Output Source Current (P-Channel)	$V_{CC} = 10V, V_{OUT} = 0V$ $T_A = 25^\circ C$	-16.0 -1.5	-25		mA mA
I_{SINK} Output Sink Current (N-Channel)	$V_{CC} = 5.0V, V_{OUT} = V_{CC}$ $T_A = 25^\circ C$	5.0	8.0		mA
I_{SINK} Output Sink Current (N-Channel)	$V_{CC} = 10V, V_{OUT} = V_{CC}$ $T_A = 25^\circ C$	20	30		mA

AC Electrical Characteristics

$T_A = 25^\circ\text{C}$, $C_L = 50\text{ pF}$, unless otherwise specified.

Parameter	Conditions	Min.	Typ.	Max.	Units
t_{ACC} Access Time from Address	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$		450 200	900 400	ns ns
t_{pd} Propagation Delay from $\overline{\text{CE}}_3$	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$		360 120	700 300	ns ns
t_{pCE1} Propagation Delay from $\overline{\text{CE}}_1$ or $\overline{\text{CE}}_2$	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$		250 85	700 200	ns ns
t_{SA} Address Setup Time	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	200 100	80 30		ns ns
t_{HA} Address Hold Time	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	50 25	15 5.0		ns ns
t_{WE} Write Enable Pulse Width	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	300 150	160 70		ns ns
t_{CE} $\overline{\text{CE}}_3$ Pulse Widths	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	400 160	200 80		ns ns
C_{IN} Input Capacity	Any Input (Note 2)		5.0		pF
C_{OUT} Output Capacity in TRI-STATE [®]	(Note 2)		9.0		pF
C_{PD} Power Dissipation Capacity	(Note 3)		400		pF

$C_L = 50\text{ pF}$

Parameter	Conditions	MM54C200 $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$		MM74C200 $T_A = -45^\circ\text{C}$ to $+85^\circ\text{C}$		Units
		Min.	Max.	Min.	Max.	
t_{ACC} Access Time from Address	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$		1200 520		1100 480	ns ns
t_{pd} Propagation Delay from $\overline{\text{CE}}_3$	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$		950 400		850 360	ns ns
$t_{\text{pd}\overline{\text{CE}}1}$ Propagation Delay from $\overline{\text{CE}}_1$ or $\overline{\text{CE}}_2$	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$		650 300		600 275	ns ns
t_{SA} Address Setup Time	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	250 120		250 120		ns ns
t_{HA} Address Hold Time	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	100 50		100 50		ns ns
t_{WE} Write Enable Pulse Width	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	450 225		400 200		ns ns
t_{CE} Disable Pulse Width	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	500 250		460 230		ns ns
t_{HD} Data Hold Time	$V_{\text{CC}} = 5.0\text{ V}$ $V_{\text{CC}} = 10\text{ V}$	50 25		50 25		ns ns

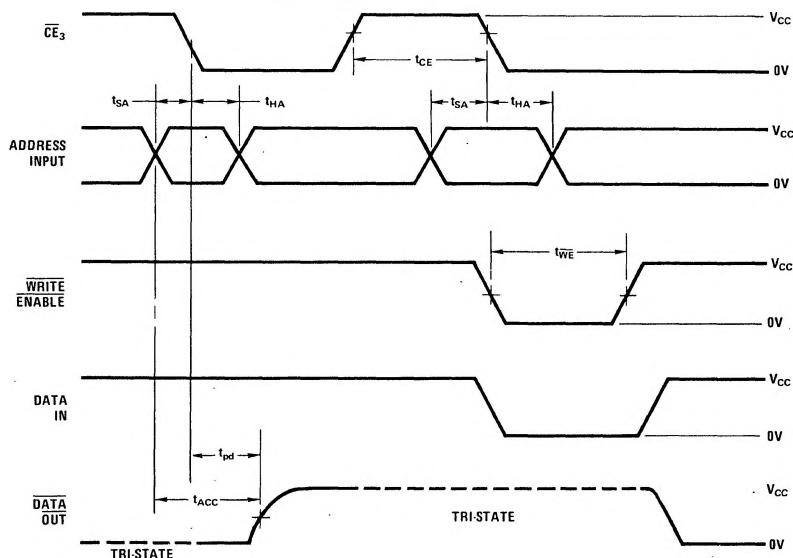
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Capacitance is guaranteed by periodic testing.

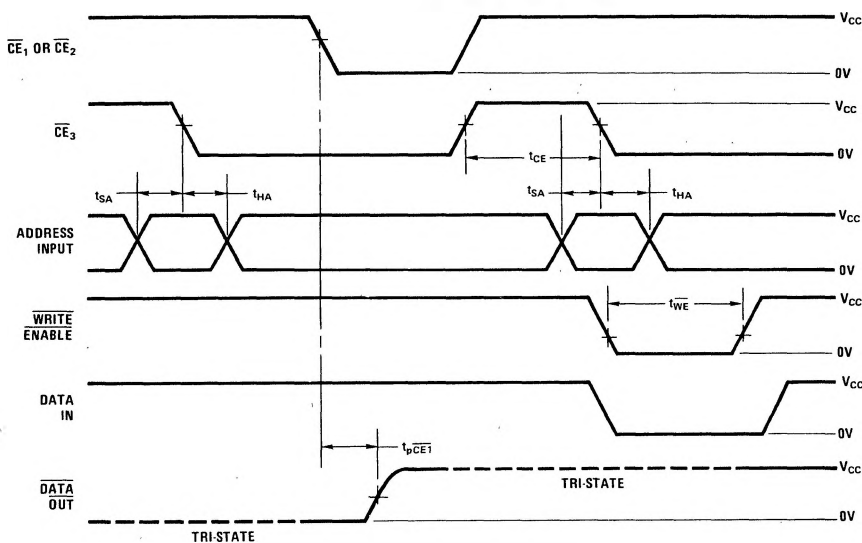
Note 3: C_{PD} determines the no load AC power consumption of any CMOS device. For complete explanation see 54C/74C Family Characteristics application note, AN-90.

Switching Time Waveforms

Read and Write Cycles Using \overline{CE}_3 ($\overline{CE}_1 = \overline{CE}_2 = \text{logic 0}$)



Read and Write Cycles Using \overline{CE}_3 and \overline{CE}_1 (or \overline{CE}_2)



Note: Used for fast access time in bused systems.